

74VHC32; 74VHCT32

Quad 2-input OR gate

Rev. 01 — 13 August 2009

Product data sheet

1. General description

The 74VHC32; 74VHCT32 are high-speed Si-gate CMOS devices and are pin compatible with Low-power Schottky TTL (LSTTL). They are specified in compliance with JEDEC standard No. 7-A.

The 74VHC32; 74VHCT32 provide the 2-input OR function.

2. Features

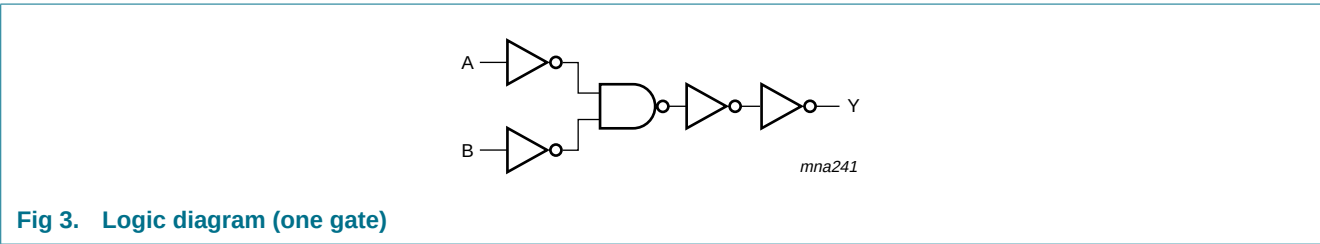
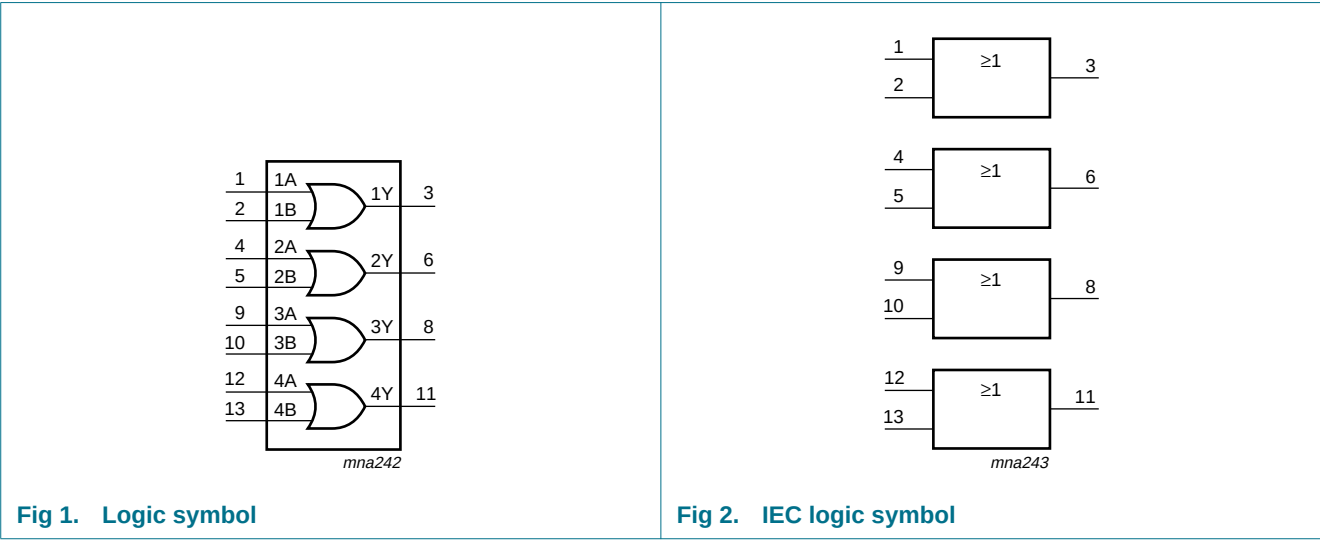
- Balanced propagation delays
- All inputs have Schmitt-trigger actions
- Inputs accept voltages higher than V_{CC}
- Input levels:
 - ◆ The 74VHC32 operates with CMOS input level
 - ◆ The 74VHCT32 operates with TTL input level
- ESD protection:
 - ◆ HBM JESD22-A114E exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
 - ◆ CDM JESD22-C101C exceeds 1000 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Ordering information

Table 1. Ordering information

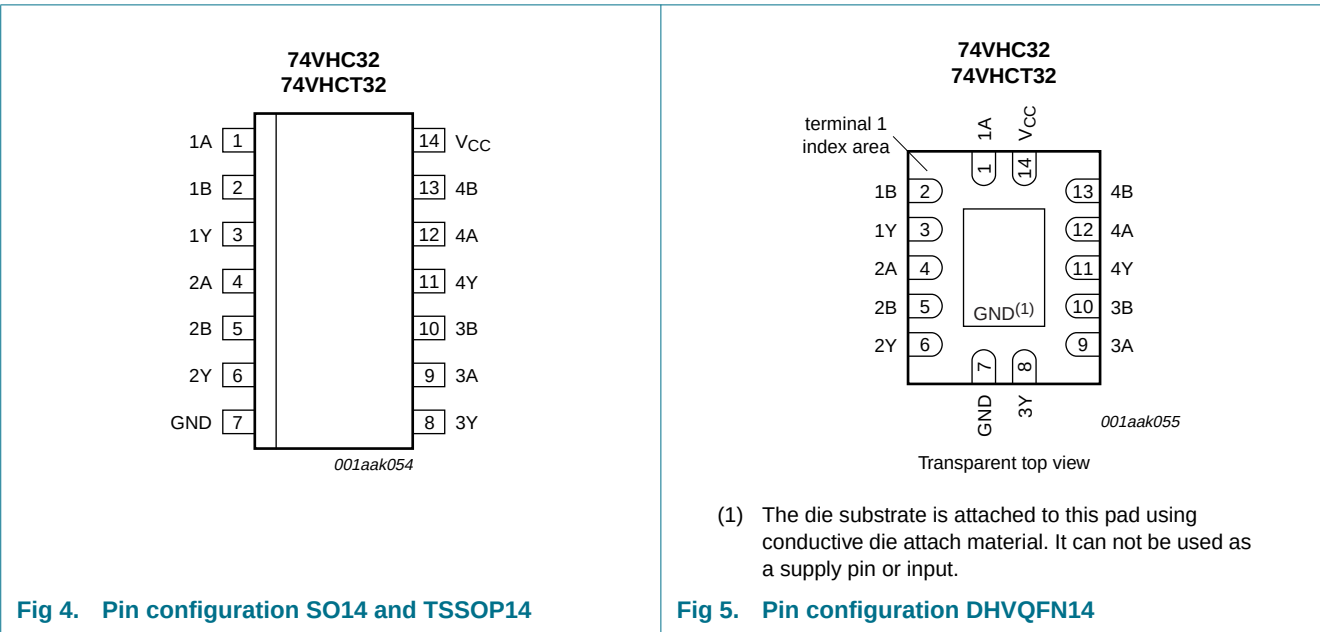
Type number	Package			
	Temperature range	Name	Description	Version
74VHC32D 74VHCT32D	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	SO14	plastic small outline package; 14 leads; body width 3.9 mm	SOT108-1
74VHC32PW 74VHCT32PW	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP14	plastic thin shrink small outline package; 14 leads; body width 4.4 mm	SOT402-1
74VHC32BQ 74VHCT32BQ	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	DHVQFN14	plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 14 terminals; body $2.5 \times 3 \times 0.85\text{ mm}$	SOT762-1

4. Functional diagram



5. Pinning information

5.1 Pinning



5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1A	1	data input
1B	2	data input
1Y	3	data output
2A	4	data input
2B	5	data input
2Y	6	data output
GND	7	ground (0 V)
3Y	8	data output
3A	9	data input
3B	10	data input
4Y	11	data output
4A	12	data input
4B	13	data input
V _{CC}	14	supply voltage

6. Functional description

Table 3. Function table^[1]

Input		Output
nA	nB	nY
L	L	L
X	H	H
H	X	H

- [1] H = HIGH voltage level;
L = LOW voltage level;
X = don't care.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
V_I	input voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5$ V	[1] -20	-	mA
I_{OK}	output clamping current	$V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V	[1] -20	+20	mA
I_O	output current	$V_O = -0.5$ V to $(V_{CC} + 0.5$ V)	-25	+25	mA
I_{CC}	supply current		-	+75	mA
I_{GND}	ground current		-75	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40$ °C to +125 °C	[2] -	500	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO14 packages: above 70 °C the value of P_{tot} derates linearly at 8 mW/K.

For TSSOP14 packages: above 60 °C the value of P_{tot} derates linearly at 5.5 mW/K.

For DHVQFN14 packages: above 60 °C the value of P_{tot} derates linearly at 4.5 mW/K.

8. Recommended operating conditions

Table 5. Operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74VHC32						
V_{CC}	supply voltage		2.0	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 3.0$ V to 3.6 V	-	-	100	ns/V
		$V_{CC} = 4.5$ V to 5.5 V	-	-	20	ns/V
74VHCT32						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	5.5	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 4.5$ V to 5.5 V	-	-	20	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit		
			Min	Typ	Max	Min	Max	Min	Max			
74VHC32												
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	-	-	1.5	-	1.5	-	V		
		V _{CC} = 3.0 V	2.1	-	-	2.1	-	2.1	-	V		
		V _{CC} = 5.5 V	3.85	-	-	3.85	-	3.85	-	V		
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	-	0.5	-	0.5	-	0.5	V		
		V _{CC} = 3.0 V	-	-	0.9	-	0.9	-	0.9	V		
		V _{CC} = 5.5 V	-	-	1.65	-	1.65	-	1.65	V		
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}										
		I _O = –50 μA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V		
		I _O = –50 μA; V _{CC} = 3.0 V	2.9	3.0	-	2.9	-	2.9	-	V		
		I _O = –50 μA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V		
		I _O = –4.0 mA; V _{CC} = 3.0 V	2.58	-	-	2.48	-	2.40	-	V		
V _{OL}	LOW-level output voltage	I _O = –8.0 mA; V _{CC} = 4.5 V	3.94	-	-	3.80	-	3.70	-	V		
		V _I = V _{IH} or V _{IL}										
		I _O = 50 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V		
		I _O = 50 μA; V _{CC} = 3.0 V	-	0	0.1	-	0.1	-	0.1	V		
		I _O = 50 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V		
I _I	input leakage current	I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.36	-	0.44	-	0.55	V		
		I _O = 8.0 mA; V _{CC} = 4.5 V	-	-	0.36	-	0.44	-	0.55	V		
		V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	μA		
		I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	2.0	-	20	-	40	μA
		C _I	input capacitance	V _I = V _{CC} or GND	-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4	-	-	-	-	-	pF		

Table 6. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74VHCT32										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –50 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –8.0 mA	3.94	-	-	3.80	-	3.70	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 50 µA	-	0	0.1	-	0.1	-	0.1	V
		I _O = 8.0 mA	-	-	0.36	-	0.44	-	0.55	V
I _I	input leakage current	V _I = 5.5 V or GND; V _{CC} = 0 V to 5.5 V	-	-	0.1	-	1.0	-	2.0	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	2.0	-	20	-	40	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V; other pins at V _{CC} or GND; I _O = 0 A; V _{CC} = 4.5 V to 5.5 V	-	-	1.35	-	1.5	-	1.5	mA
C _I	input capacitance	V _I = V _{CC} or GND	-	3	10	-	10	-	10	pF
C _O	output capacitance		-	4	-	-	-	-	-	pF

10. Dynamic characteristics

Table 7. Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74VHC32										
t _{pd}	propagation delay	nA, nB to nY; see Figure 6	[2]							
		V _{CC} = 3.0 V to 3.6 V								
		C _L = 15 pF	-	3.9	7.9	1.0	9.5	1.0	10.0	ns
		C _L = 50 pF	-	5.6	11.4	1.0	13	1.0	14.5	ns
		V _{CC} = 4.5 V to 5.5 V								
		C _L = 15 pF	-	2.8	5.5	1.0	6.5	1.0	7.0	ns
		C _L = 50 pF	-	4.1	7.5	1.0	8.5	1.0	9.5	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC}	[3]	-	10	-	-	-	-	pF

Table 7. Dynamic characteristics ...continued
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74VHCT32; V_{CC} = 4.5 V to 5.5 V										
t _{pd}	propagation delay	nA, nB to nY; see Figure 6 ^[2]								
		C _L = 15 pF	-	3.1	6.9	1.0	8.0	1.0	9.0	ns
		C _L = 50 pF	-	4.3	7.9	1.0	9.0	1.0	10.0	ns
C _{PD}	power dissipation capacitance	f _i = 1 MHz; V _I = GND to V _{CC} ^[3]	-	12	-	-	-	-	-	pF

- [1] Typical values are measured at nominal supply voltage (V_{CC} = 3.3 V and V_{CC} = 5.0 V).
- [2] t_{pd} is the same as t_{PLH} and t_{PHL}.
- [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
 f_i = input frequency in MHz;
 f_o = output frequency in MHz;
 C_L = output load capacitance in pF;
 V_{CC} = supply voltage in V;
 N = number of inputs switching;
 Σ(C_L × V_{CC}² × f_o) = sum of the outputs.

11. Waveforms

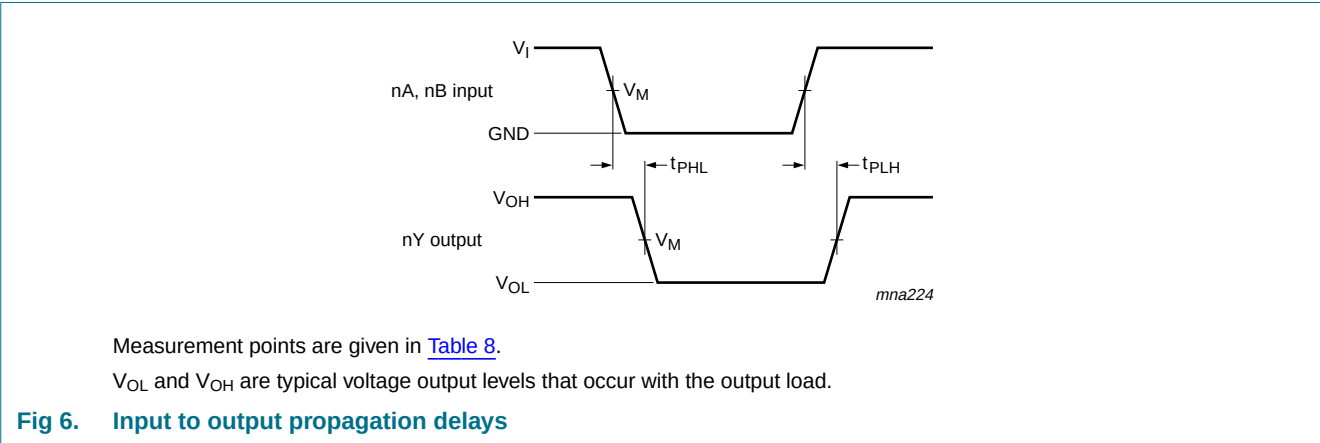
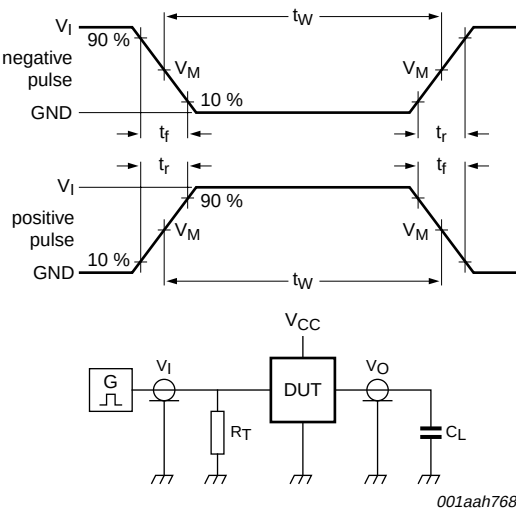


Table 8. Measurement points

Type	Input	Output
	V _M	V _M
74VHC32	0.5V _{CC}	0.5V _{CC}
74VHCT32	1.5 V	0.5V _{CC}



Test data is given in [Table 9](#).
Definitions test circuit:
 R_T = termination resistance should be equal to output impedance Z_o of the pulse generator.
 C_L = load capacitance including jig and probe capacitance.

Fig 7. Load circuitry for measuring switching times

Table 9. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74VHC32	V_{CC}	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74VHCT32	3.0 V	≤ 3.0 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO14: plastic small outline package; 14 leads; body width 3.9 mmSOT108-1

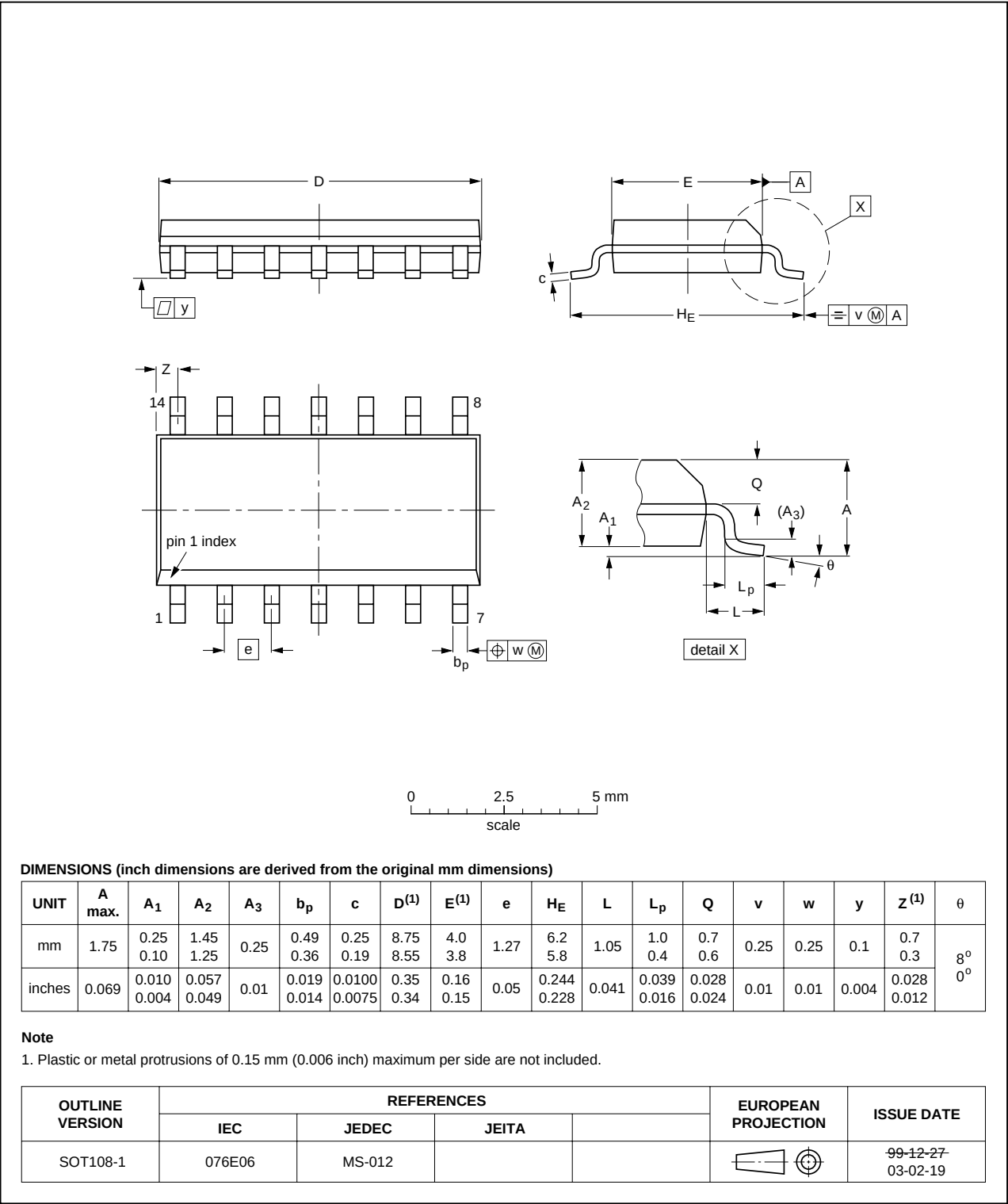


Fig 8. Package outline SOT108-1 (SO14)

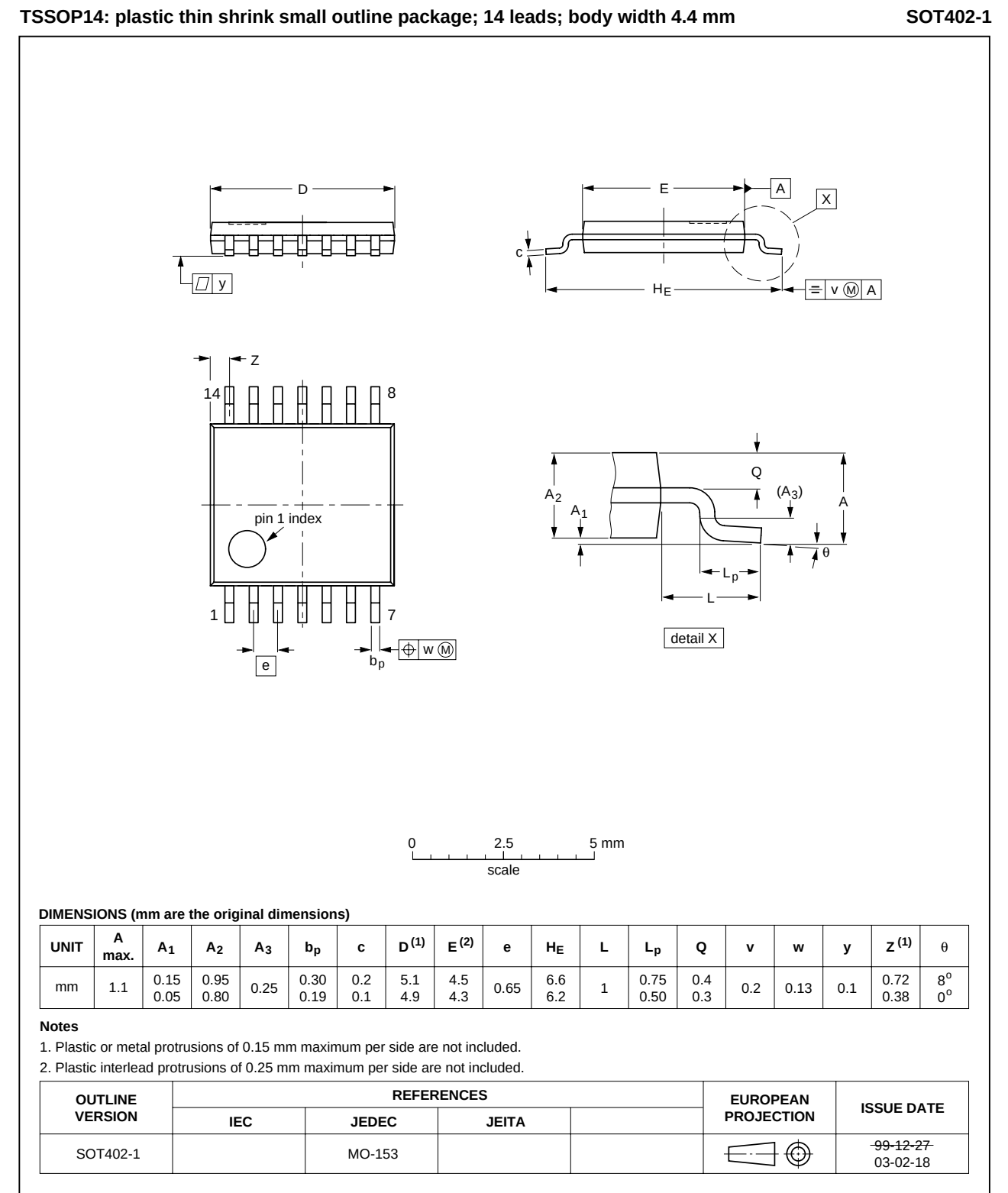


Fig 9. Package outline SOT402-1 (TSSOP14)

DHVQFN14: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads;
14 terminals; body 2.5 x 3 x 0.85 mm

SOT762-1

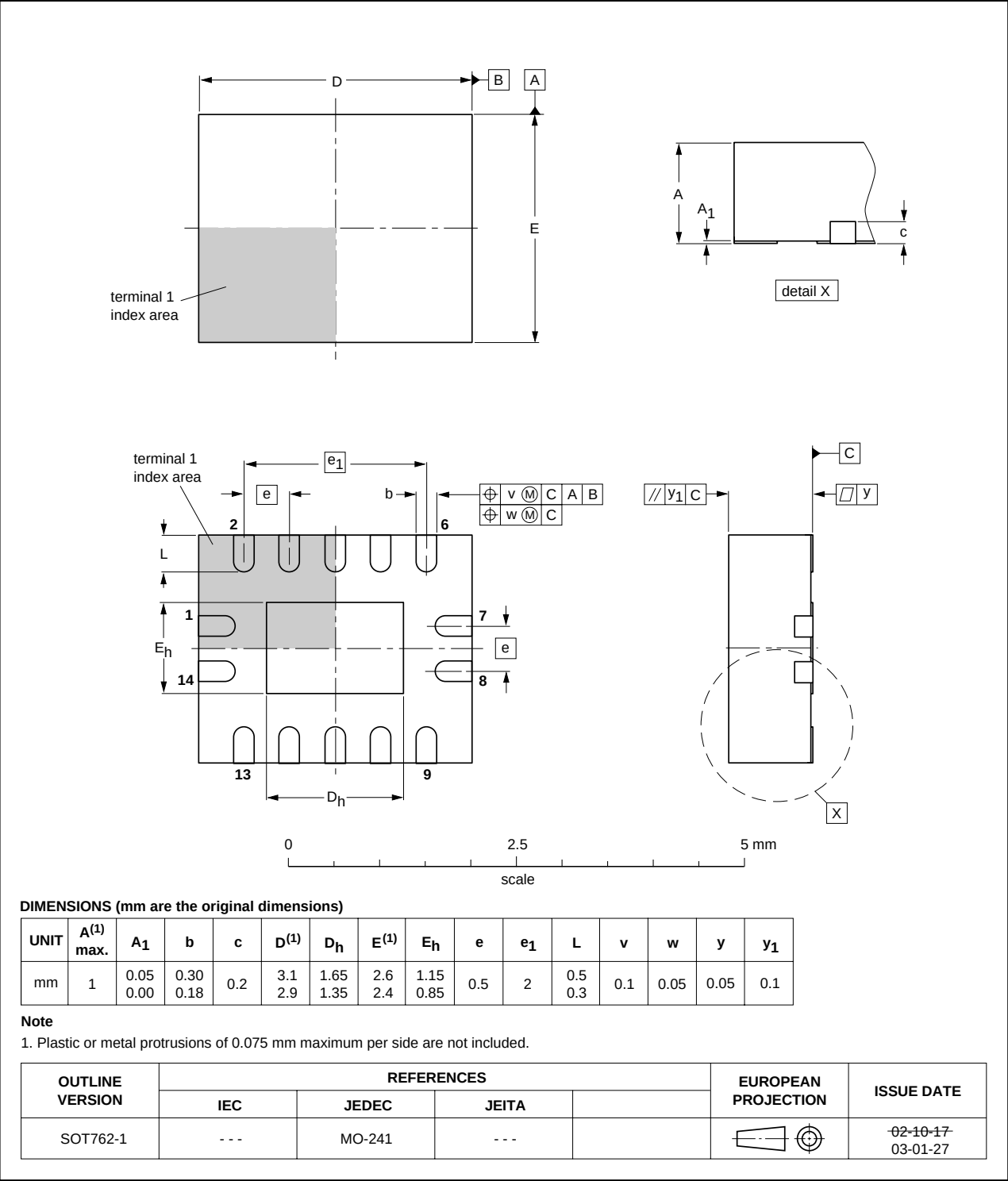


Fig 10. Package outline SOT762-1 (DHVQFN14)

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
LSTTL	Low-power Schottky Transistor-Transistor Logic
MM	Machine Model

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74VHC_VHCT32_1	20090813	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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[2] The term 'short data sheet' is explained in section "Definitions".

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